Bridge Rectifier

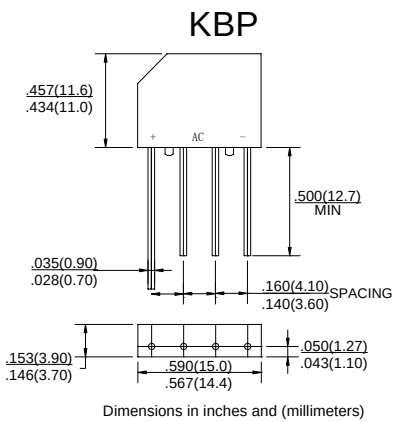
■ Features

- I_o 3A
- V_{RRM} 50V~1000V
- Glass passivated chip
- High surge forward current capability

■ Applications

- General purpose 1 phase Bridge rectifier applications

■ Outline Dimensions and Mark



■ Limiting Values(Absolute Maximum Rating)

Item	Symbol	Unit	Conditions	KBP3						
				005	01	02	04	06	08	10
Repetitive Peak Reverse Voltage	V_{RRM}	V		50	100	200	400	600	800	1000
Average Rectified Output Current	I_O	A	60H_Z sine wave, R- load, T_a=30℃	3						
Surge(Non-repetitive)Forward Current	I_{FSM}	A	60H_Z sine wave, 1 cycle, T_a=25℃	80						
Current Squared Time	I^2t	A^2s	1ms≤t＜8.3ms T_j=25℃,Rating of per diode	26.5						
Storage Temperature	T_{stg}	℃		-55 ~+150						
Junction Temperature	T_j	℃		-55 ~+150						

■ Electrical Characteristics（T_a=25℃ Unless otherwise specified）

Item	Symbol	Unit	Test Condition	Max
Peak Forward Voltage	V_{FM}	V	I_{FM}=3A, Pulse measu ement Rating of per diode	1.1
Peak Reverse Current	I_{RRM}	μA	V_{RM}=V_{RRM} , Pulse measurement, Rating of per diode	10
Thermal Resistance(1)	$R_{\theta J\text{-}A}$	℃/W	Between junction and ambient	20
	$R_{\theta J\text{-}L}$		Between junction and lead	11

Notes :

（1）Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.47×0.47"(12×12mm) copper pads

■ Characteristics(Typical)

FIG1:Io-Ta Curve

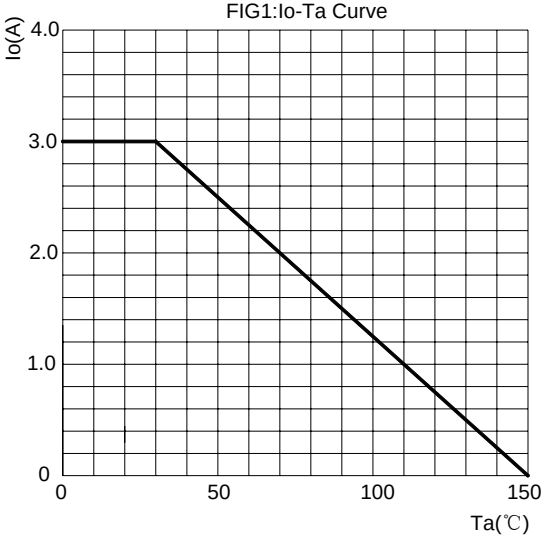


FIG2:Surge Forward Current Capadility

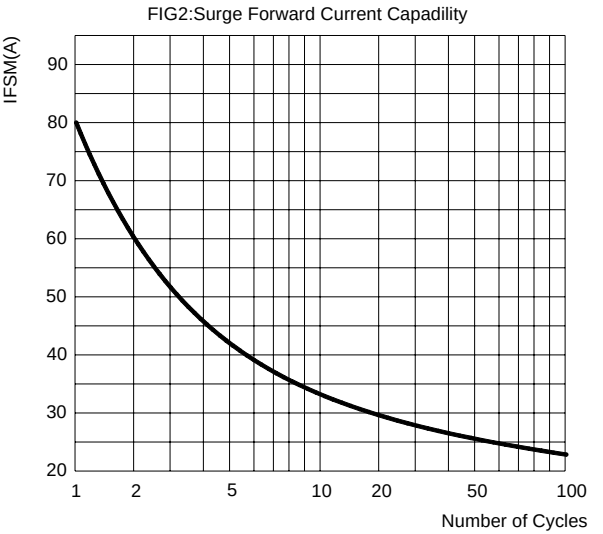


FIG3:Instantaneous Forward Voltage

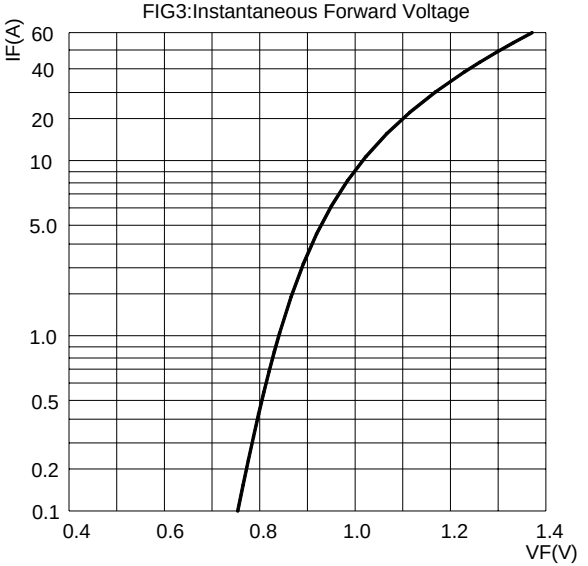


FIG4:Typical Reverse Characteristics